

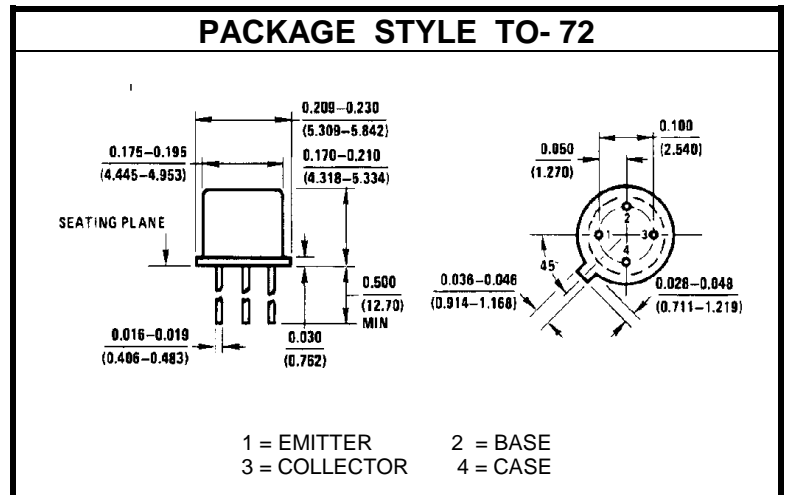
NPN SILICON HIGH FREQUENCY TRANSISTOR

DESCRIPTION:

The **2N3570** is Designed for High Frequency Low Noise Amplifier and Oscillator Applications.

MAXIMUM RATINGS

I_C	50 mA
V_{CB}	30 V
V_{CE}	15 V
V_{EB}	3.0 V
P_{DISS}	200 mW @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+200^\circ C$
θ_{JC}	500 $^\circ C/W$


CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 2 \text{ mA}$		15			V
BV_{CBO}	$I_C = 1.0 \mu A$		30			V
I_{CBO}	$V_{CB} = 6.0 \text{ V}$				10 1.0	μA
$T_A = 150^\circ C$						
BV_{EBO}	$I_E = 10 \mu A$		3.0			V
h_{FE}	$V_{CE} = 6.0 \text{ V}$	$I_C = 5.0 \text{ mA}$	20		150	---
C_{ob}	$V_{CB} = 6 \text{ V}$	$f = 1.0 \text{ MHz}$			0.75	pF
h_{FE}	$V_{CE} = 6 \text{ V}$	$I_C = 5 \text{ mA}$	20		150	---
$ h_{fe} $	$V_{CE} = 6 \text{ V}$	$I_C = 5 \text{ mA}$	3.75	4.25	6	---
$r_b \text{ } \dot{C}_C$	$V_{CB} = 6 \text{ V}$	$I_E = -5 \text{ mA}$	1	5	8	pF
P_{osc}	$V_{CC} = 20 \text{ V}$	$I_C = 15 \text{ mA}$		60		mW
N_F	$V_{CB} = 6 \text{ V}$	$I_C = 2 \text{ mA}$	$R_G = 50 \Omega$	6	7	dB